L Number	Hits	Search Text	DB	Time stamp
-	0	Fullford-Jim-H.in.	USPAT	2003/10/03 14:24
-	1	Fullford.in.	USPAT	2004/01/23 13:51
-	38360	semiconductor and ((depth or thickness) same temperature)	USPAT	2004/01/23 13:56
-	23673	(semiconductor and ((depth or thickness) same temperature)) and (etch or etching)	USPAT	2002/09/11 15:52
-	14691	semiconductor and ((depth or thickness) with temperature)	USPAT	2002/09/11 15:56
-	5285	(semiconductor and ((depth or thickness) with temperature)) and plasma	USPAT	2002/09/11 15:56
-	2028	((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))	USPAT	2002/09/11 16:00
-	1519	(((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((temperature or depth or thickness).ab. (temperature or depth or thickness).clm.)	USPAT	2002/09/11 16:03
-	1177	(((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)	USPAT	2002/09/11 16:03
-	607	((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)	USPAT	2002/09/11 16:04
-	454	(((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and (etch or etching)	USPAT	2002/09/11 16:04
-	214	(((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)	USPAT	2002/09/11 16:05
-	214	((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001	USPAT	2002/09/12 08:45
-	214	((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001	USPAT	2004/01/23 13:57

-	183	((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001) and @py<=2001	USPAT	2002/09/12 11:40
-	751	fulford	USPAT	2002/09/12 11:40
-	315	fulford.in.	USPAT	2002/09/12 11:45
-	0	fulford-Jim.in.	USPAT	2002/09/12 11:41
-	2	fulford-Jim-H.in.	USPAT	2002/09/12 11:41
-	2	("5733812" | "5789780").PN.	USPAT	2002/09/12 11:42
-	9	5863824.URPN.	USPAT	2002/09/12 11:43
-	504	fulford and semiconductor	USPAT	2002/09/12 11:45
-	266	fulford.in. and semiconductor	USPAT	2002/09/12 11:45
-	254	(fulford.in. and semiconductor) and (depth or thickness)	USPAT	2002/09/12 11:47
-	192	((fulford.in. and semiconductor) and (depth or thickness)) and @py<=2000	USPAT	2002/09/12 13:37
-	142	(depth and thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)	USPAT	2002/09/12 13:59
-	40	((depth and thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor	USPAT	2002/09/12 13:40
-	8085	(depth or thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)	USPAT	2002/09/12 14:02
-	1783	((depth or thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor	USPAT	2002/09/12 14:00
-	551	(((depth or thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor) and plasma	USPAT	2002/09/12 14:01
-	527	((((depth or thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor) and plasma) not (((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001) and @py<=2001)	USPAT	2002/09/12 14:01

-	514	(((((depth or thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor) and plasma) not (((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001) and @py<=2001)) not (((depth and thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor)	USPAT	2002/09/12 14:01
-	372	((((((depth or thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor) and plasma) not (((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001) and @py<=2001)) not (((depth and thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor)) and (etch or etching)	USPAT	2002/09/12 14:03
-	372	(((((((depth or thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor) and plasma) not (((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001) and @py<=2001)) not (((depth and thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor)) and (etch or etching)) and @ay<=2001	USPAT	2002/09/12 14:04
-	370	(((((((depth or thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor) and plasma) not (((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001) and @py<=2001)) not (((depth and thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor)) and (etch or etching)) and @ay<=2001) not fulford.in.	USPAT	2002/09/12 14:04

-	368	(((((((((depth or thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor) and plasma) not (((((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001) and @py<=2001)) not (((depth and thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor)) and (etch or etching)) and @ay<=2001) not fulford.in.) not (((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001)	USPAT	2002/09/12 14:05
-	232	((((((((((depth or thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor) and plasma) not (((((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001) and @py<=2001)) not (((depth and thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor)) and (etch or etching)) and @ay<=2001) not fulford.in.) not (((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001)) and (opening or trench or hole)	USPAT	2002/09/12 14:06

-	203	((((((((((depth or thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor) and plasma) not (((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001) and @py<=2001)) not (((depth and thickness) with temperature with (change or changing or adjust$3 or vary or varied or varing)) and semiconductor)) and (etch or etching)) and @ay<=2001) not fulford.in.) not (((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur$4 or compar$3 or determin$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001)) and (opening or trench or hole)) and (measur$4 or compar$3 or determin$3)	USPAT	2002/09/12 14:14
-	141	((depth or thickness).ab. with temperature) and semiconductor and plasma	USPAT	2004/02/02 17:33
-	1	5375064.pn.	USPAT	2002/09/16 14:29
-	4	5375064.URPN.	USPAT	2002/09/16 13:06
-	5	("5082517" | "5375064" | "5376224" | "5680014" | "5688415").PN.	USPAT	2002/09/16 13:06
-	14462	(temperature with control or controller) same (depth or thickness)	USPAT	2002/09/16 13:17
-	840	((temperature with control or controller) same (depth or thickness)) and semiconductor and plasma and ((contact adj hole) or opening or via or trench)	USPAT	2002/09/16 13:19
-	247	(((temperature with control or controller) same (depth or thickness)) and semiconductor and plasma and ((contact adj hole) or opening or via or trench)) and photo$1resist	USPAT	2002/09/16 13:19
-	244	((((temperature with control or controller) same (depth or thickness)) and semiconductor and plasma and ((contact adj hole) or opening or via or trench)) and photo$1resist) not (((depth or thickness).ab. with temperature) and semiconductor and plasma)	USPAT	2002/09/16 13:22
-	233	(((((temperature with control or controller) same (depth or thickness)) and semiconductor and plasma and ((contact adj hole) or opening or via or trench)) and photo$1resist) not (((depth or thickness).ab. with temperature) and semiconductor and plasma)) and (etch or etching)	USPAT	2002/09/16 13:22

-	98	((((((temperature with control or controller) same (depth or thickness)) and semiconductor and plasma and ((contact adj hole) or opening or via or trench)) and photo$1resist) not (((depth or thickness).ab. with temperature) and semiconductor and plasma)) and (etch or etching)) and (temperature with (zone or area or region))	USPAT	2002/09/16 14:29
-	0	364/474.3.ccls.	USPAT	2002/09/16 14:30
-	0	364/474.ccls.	USPAT	2002/09/16 14:31
-	0	700/188.pn.	USPAT	2002/09/16 14:32
-	176	700/188.ccls.	USPAT	2002/09/16 14:32
-	7	700/188.ccls. and semiconductor	USPAT	2002/09/16 14:34
-	189	216/59.ccls.	USPAT	2002/09/16 14:35
-	117	216/59.ccls. and temperature	USPAT	2002/09/16 14:35
-	117	(216/59.ccls. and temperature) not (((((((temperature with control or controller) same (depth or thickness)) and semiconductor and plasma and ((contact adj hole) or opening or via or trench)) and photo$1resist) not (((depth or thickness).ab. with temperature) and semiconductor and plasma)) and (etch or etching)) and (temperature with (zone or area or region)))	USPAT	2002/09/16 14:35
-	116	(216/59.ccls. and temperature) not (((depth or thickness).ab. with temperature) and semiconductor and plasma)	USPAT	2002/09/16 14:35
-	87	((216/59.ccls. and temperature) not (((depth or thickness).ab. with temperature) and semiconductor and plasma)) and (depth or thickness)	USPAT	2002/09/16 14:36
-	2	5795493.pn. 5375064.pn.	USPAT	2003/10/03 14:25
-	3	Fulford-Jim-H.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 13:52
-	13	Lansford-Jeremy.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 13:54
-	64617	semiconductor and ((depth or thickness) same temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 14:06
-	20409	(semiconductor and ((depth or thickness) same temperature)) and @ay<=2001 and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 14:07
-	25790	semiconductor and ((depth or thickness) with temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 14:07

-	7495	(semiconductor and ((depth or thickness) with temperature)) and @ay<=2001 and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 14:11
-	2890	((semiconductor and ((depth or thickness) with temperature)) and @ay<=2001 and plasma) and ((measur$4 or compar$3 or determin$3 or calulat$3) with (depth or thickness))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 14:25
-	668	((semiconductor and ((depth or thickness) with temperature)) and @ay<=2001 and plasma) and ((measur$4 or compar$3 or determin$3 or calulat$3) with (depth or thickness) with temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 14:26
-	474	(((semiconductor and ((depth or thickness) with temperature)) and @ay<=2001 and plasma) and ((measur$4 or compar$3 or determin$3 or calulat$3) with (depth or thickness) with temperature)) and (etch or etching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 14:34
-	392	((((semiconductor and ((depth or thickness) with temperature)) and @ay<=2001 and plasma) and ((measur$4 or compar$3 or determin$3 or calulat$3) with (depth or thickness) with temperature)) and (etch or etching)) and @ad<=20010327	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 16:32
-	474	((((semiconductor and ((depth or thickness) with temperature)) and @ay<=2001 and plasma) and ((measur$4 or compar$3 or determin$3 or calulat$3) with (depth or thickness) with temperature)) and (etch or etching))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 16:33
-	1806	(depth or thickness) with temperature with (etch or etching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 16:33
-	678	((depth or thickness) with temperature with (etch or etching)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 16:33
-	594	(((depth or thickness) with temperature with (etch or etching)) and plasma) and @ay<=2001	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 16:34
-	396	((depth or thickness).ab. with temperature) and semiconductor and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 17:33
-	371	(((depth or thickness).ab. with temperature) and semiconductor and plasma) and @ay<=2001	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 17:34